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KAF-3200

2184 (H) x 1472 (V) Full Frame CCD Image Sensor

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Description

The KAF−3200 Image Sensor is a high performance CCD (charge−coupled device) with 2184 (H) x 1472 (V) photoactive pixels designed for a wide range of image sensing applications.

The sensor incorporates true two−phase CCD technology, simplifying the support circuits required to drive the sensor as well as reducing dark current without compromising charge capacity. The sensor also utilizes the TRUESENSE Transparent Gate Electrode to improve sensitivity compared to the use of a standard front side illuminated polysilicon electrode.

Table 1. GENERAL SPECIFICATIONS

Parameter	Typical Value
Architecture	Full Frame CCD
Total Number of Pixels	2184 (H) x 1510 (V)
Number of Active Pixels	2184 (H) x 1472 (V)
Pixel Size	6.8 μm (H) x 6.8 μm (V)
Active Imager Size	14.85 mm (H) x 10.26 mm (V) 18 mm (diag), 4/3” optical format
Optical Fill−Factor	100%
Saturation Signal	55,000 electrons
Output Sensitivity	12 μV/e−
Readout Noise (1 MHz)	7 electrons rms
Dark Current (25°C, Accumulation Mode)	< 7 pA/cm^2
Dark Current Doubling Rate	6°C
Dynamic Range (Sat Sig / Dark Noise)	78 dB
Quantum Efficiency with microlenses (Red, Green, Blue)	55%, 70%, 80%
Maximum Data Rate	15 MHz
Package	CERDIP Package (sidebrazed)
Cover Glass	Clear or AR coated, 2 sides

NOTE: Parameters above are specified at T = 25°C unless otherwise noted.

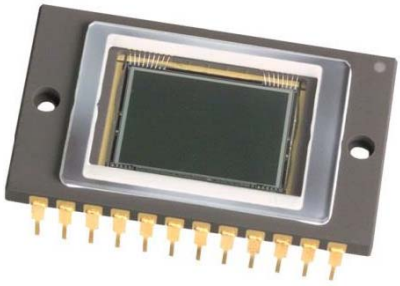


Figure 1. KAF−3200 CCD Image Sensor

Features

- True Two Phase Full Frame Architecture
- TRUESENSE Transparent Gate Electrode for High Sensitivity
- 100% Fill Factor
- Low Dark Current
- Microlenses
- High Output Sensitivity

Applications

- Medical Imaging
- Scientific Imaging

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ORDERING INFORMATION

Table 2. ORDERING INFORMATION

Part Number	Description	Marking Code
KAF−3200−ABA−CD−B2	Monochrome, Telecentric Microlens, CERDIP Package (sidebrazed), Clear Cover Glass with AR coating (both sides), Grade 2	KAF−3200−ABA (Serial Number)
KAF−3200−ABA−CD−AE	Monochrome, Telecentric Microlens, CERDIP Package (sidebrazed), Clear Cover Glass with AR coating (both sides), Engineering Sample	
KAF−3200−ABA−CP−B2	Monochrome, Telecentric Microlens, CERDIP Package (sidebrazed), Taped Clear Cover Glass, no coatings, Grade 2	KAF−3200−ABA (Serial Number)
KAF−3200−ABA−CP−AE	Monochrome, Telecentric Microlens, CERDIP Package (sidebrazed), Taped Clear Cover Glass, no coatings, Engineering Sample	
KAF−3200−12−5−A−EVK	Evaluation Board (Complete Kit)	N/A

See the ON Semiconductor *Device Nomenclature* document (TND310/D) for a full description of the naming convention used for image sensors. For reference documentation, including information on evaluation kits, please visit our web site at www.onsemi.com.

DEVICE DESCRIPTION

Architecture

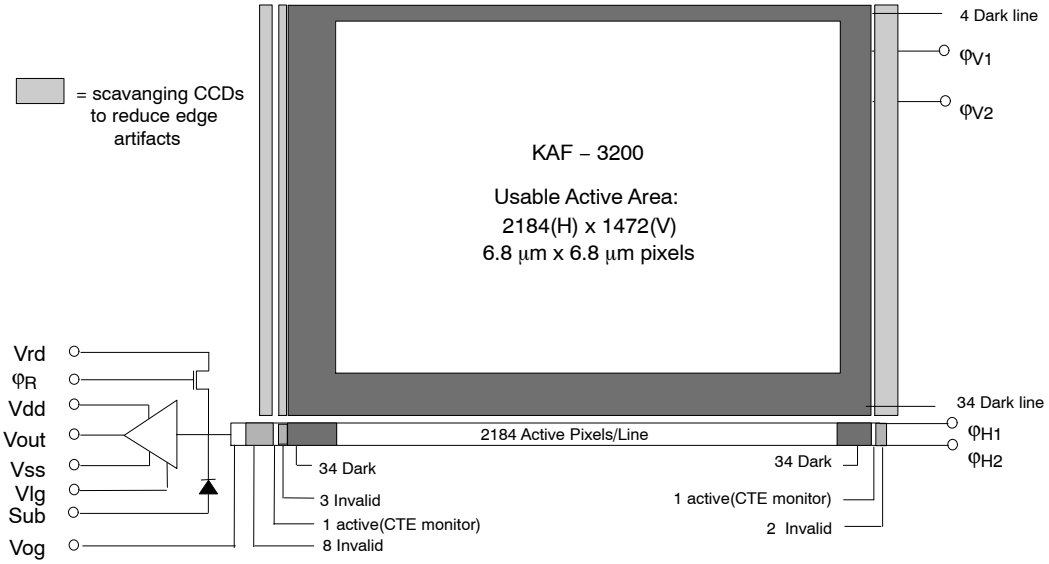


Figure 2. Block Diagram

The sensor is built with a true two−phase CCD technology employing a transparent gate and with microlenses available. This technology simplifies the support circuits that drive the sensor and reduces the dark current without compromising charge capacity. The transparent gate results in spectral response increased ten times at 400 nm, compared to a front side illuminated standard poly silicon gate technology. The micro lenses are an integral part of each pixel and cause most of the light to pass through the transparent gate half of the pixel, further improving the spectral sensitivity.

The photoactive area is 14.85 mm x 10.26 mm and is housed in a 24 pin, dual in line (DIP) package with 0.1” pin spacing.

The sensor consists of 2254 parallel (vertical) CCD shift registers each 1510 elements long. These registers act as both the photosensitive elements and as the transport circuits that allow the image to be sequentially read out of the sensor. The parallel (vertical) CCD registers transfer the image one line at a time into a single 2267 element (horizontal) CCD shift register. The horizontal register transfers the charge to a single output amplifier. The output amplifier is a two−stage source follower that converts the photo−generated charge to a voltage for each pixel.

Dark Reference Pixels

At the beginning of each line are 34 light shielded pixels. There are also 34 full dark lines at the start of every frame and 4 full dark lines at the end of each frame. Under normal circumstances, the pixels in these dark lines do not respond to light. However, dark reference pixels in close proximity to an active pixel, (including the 2 full dark lines and one column at end of each line), can scavenge signal depending on light intensity and wavelength and therefore will not represent the true dark signal.

Output Structure

Charge presented to the floating diffusion (FD) is converted into a voltage and current amplified in order to drive off−chip loads. The resulting voltage change seen at the output is linearly related to the amount of charge placed on FD. Once the signal has been sampled by the system electronics, the reset gate (φR) is clocked to remove the signal and FD is reset to the potential applied by VRD. More signal at the floating diffusion reduces the voltage seen at the output pin. In order to activate the output structure, an off−chip load must be added to the Vout pin of the device. See Figure 3.

Transfer Efficiency Test Pixels and Dummy Pixels

At the beginning of each line and at the end of each line are extra horizontal CCD pixels. These are a combination of pixels that are not associated with any vertical CCD register and two that are associated with extra photoactive vertical CCDs. These are provided to give an accurate photosensitive signal that can be used to monitor the charge transfer efficiency in the serial (horizontal) register.

They are arranged as follows beginning with the first pixel in each line.

- 8 dark, inactive pixels
- 1 photoactive
- 3 inactive pixels
- 34 dark reference pixels
- 2184 photoactive pixels
- 34 dark pixels
- 1 photo active pixel
- 2 inactive pixels

Image Acquisition

An electronic representation of an image is formed when incident photons falling on the sensor plane create electron−hole pairs within the sensor. These photon−induced electrons are collected locally by the formation of potential wells at each pixel site. The number of electrons collected is linearly dependent on light level and exposure time, and non−linearly dependent on wavelength. When the pixel's capacity is reached, excess electrons will leak into the adjacent pixels within the same column. This is termed blooming. During the integration period, the φV1 and φV2 register clocks are held at a constant (low) level. See Figure 7.

Charge Transport

Referring to Figure 8, the integrated charge from each photo−gate is transported to the output using a two−step process. Each line (row) of charge is first transported from the vertical CCDs to the horizontal CCD register using the φV1 and φV2 register clocks. The horizontal CCD is presented a new line on the falling edge of φV1 while φH2 is held high. The horizontal CCD's then transport each line, pixel by pixel, to the output structure by alternately clocking the φH1 and φH2 pins in a complementary fashion. On each falling edge of φH1 a new charge packet is transferred onto a floating diffusion and sensed by the output amplifier.

Horizontal Register

Output Structure

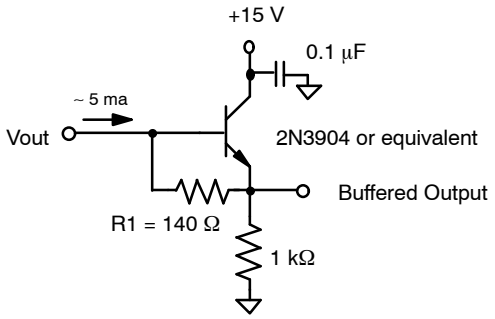


Figure 3. Output Structure Load Diagram

Notes:

1. For Operation of up to 10 MHz.
2. The value of R1 depends on the desired output current according the following formula: R1 = 0.7 / Iout
3. The optimal output current depends on the capacitance that needs to be driven by the amplifier and the bandwidth required. 5 mA is recommended for capacitance of 12 pF and pixel rates up to 15 MHz.

PHYSICAL DESCRIPTION

Pin Description and Device Orientation

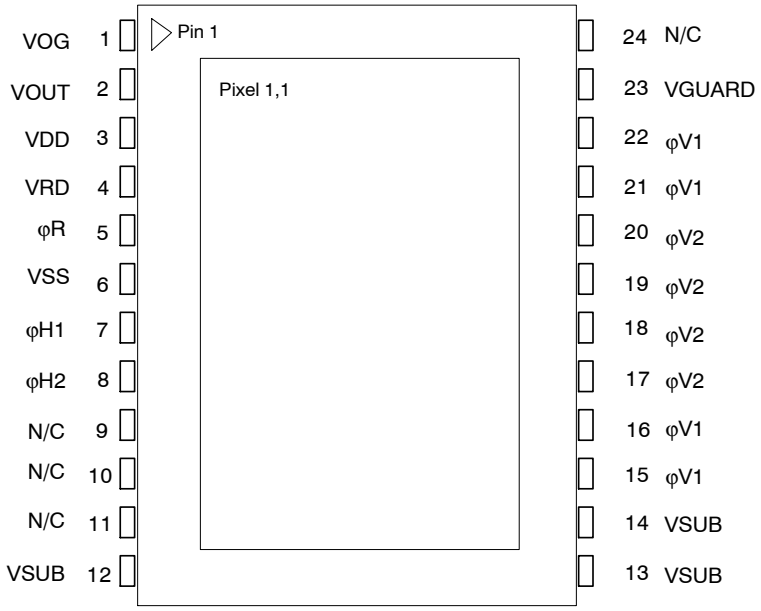


Figure 4. Pinout Diagram

NOTE: The KAF−3200 is designed to be compatible with the KAF−1602 and KAF−0401 series of Image sensors. The exception is the addition of two new Vsub connections on pins 12 and 13.

Table 3. PIN DESCRIPTION

Pin	Name	Description
1	VOG	Output Gate
2	VOUT	Video Output
3	VDD	Amplifier Supply
4	VRD	Reset Drain
5	φR	Reset Clock
6	VSS	Amplifier Supply Return
7	φH1	Horizontal CCD Clock − Phase 1
8	φH2	Horizontal CCD Clock − Phase 2
9	N/C	No Connection (open pin)
10	N/C	No Connection (open pin)
11	N/C	No Connection (open pin)
12	VSUB	Substrate (Ground)

Pin	Name	Description
24	N/C	No Connection (open pin)
23	VGUARD	Substrate (Ground)
22	φV1	Vertical CCD Clock − Phase 1
21	φV1	Vertical CCD Clock − Phase 1
20	φV2	Vertical CCD Clock − Phase 2
19	φV2	Vertical CCD Clock − Phase 2
18	φV2	Vertical CCD Clock − Phase 2
17	φV2	Vertical CCD Clock − Phase 2
16	φV1	Vertical CCD Clock − Phase 1
15	φV1	Vertical CCD Clock − Phase 1
14	VSUB	Substrate (Ground)
13	VSUB	Substrate (Ground)

IMAGING PERFORMANCE

Typical Operational Conditions

All values measured at 25°C, and nominal operating conditions. These parameters exclude defective pixels.

Table 4. SPECIFICATIONS

Description	Symbol	Min	Nom.	Max	Units	Notes	Verification Plan
Saturation Signal	Nsat				e^-/pixel	1	design[11]
Vertical CCD Capacity		50,000	55,000				
Horizontal CCD Capacity		100,000	110,000				
Output Node Capacity		100,000	110,000	120,000			
Quantum Efficiency with Microlenses					%QE	3	
Red		55					design[11]
Blue		70					design[11]
Green		80					design[11]
Photoresponse Non−Linearity	PRNL		1	2	%	2	design[11]
Photoresponse Non−Uniformity	PRNU		1	3	%	3	die[10]
Dark Signal	Jdark		15 6	30 10	e^-/ pixel / s pA/cm^2	4	die[10]
Dark Signal Doubling Temperature		5	6	7	°C		design[11]
Dark Signal Non−Uniformity	DSNU		15	30	e^-/ pixel / s	5	die[10]
Dynamic Range	DR	72	77		dB	6	design[118]
Charge Transfer Efficiency	CTE	0.99997	0.99999				die[10]
Output Amplifier DC Offset	Vodc	Vrd − 2	Vrd − 1	Vrd	V	7	die[10]
Output Amplifier Bandwidth	f_{-3dB}		45		MHz	8	design[11]
Output Amplifier Sensitivity	Vout/ne^-	18	20		μV/e^-		design[11]
Output Amplifier Output Impedance	Zout	175	200	250	Ω		design[11]
Noise Floor	ne^-		7	12	electrons	9	die[10]

1. For pixel binning applications, electron capacity up to 150,000 can be achieved with modified CCD inputs. Each sensor may have to be optimized individually for these applications. Some performance parameters may be compromised to achieve the largest signals.
2. Worst case deviation from straight line fit, between 2% and 90% of Nsat.
3. One Sigma deviation of a 128 x 128 sample when CCD illuminated uniformly.
4. Average of all pixels with no illumination at 25°C.
5. Average dark signal of any of 11 x 8 blocks within the sensor. (Each block is 128 x 128 pixels)
6. 20log (Nsat / ne^-) at nominal operating frequency and 25°C.
7. Video level offset with respect to ground.
8. Last output amplifier stage only. Assumes 10 pF off−chip load.
9. Output noise at −10°C, 1 MHz operating frequency (15 MHz bandwidth), and tint = 0 (excluding dark signal).
10. A parameter that is measured on every sensor during production testing.
11. A parameter that is quantified during the design verification activity.

TYPICAL PERFORMANCE CURVES

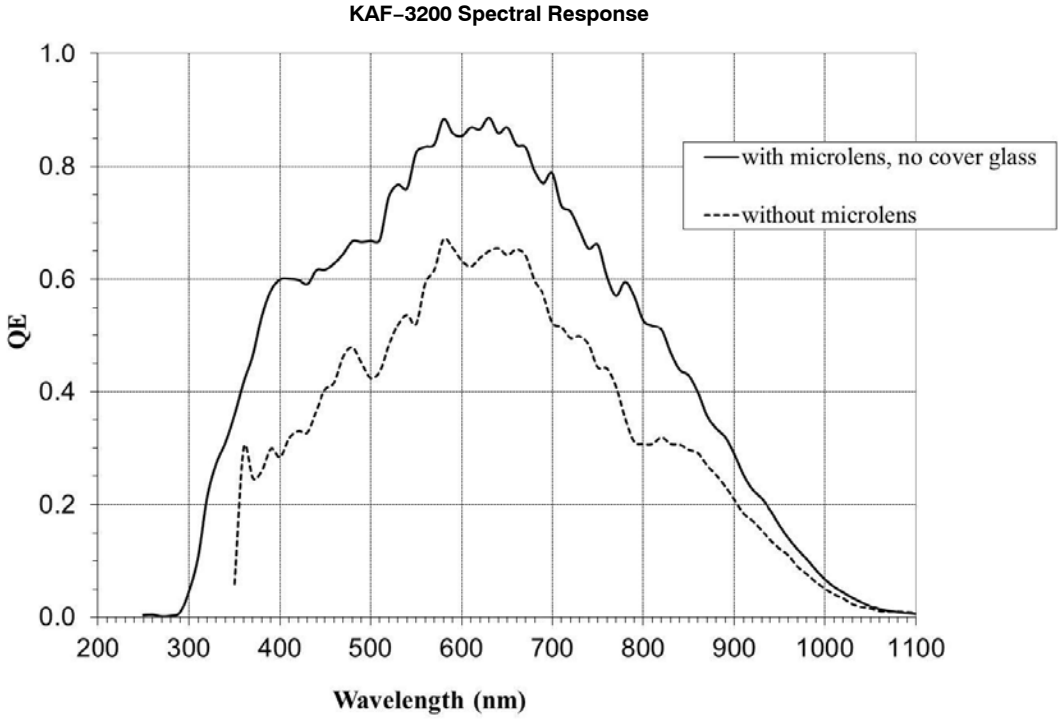


Figure 5. Typical Spectral Response

DEFECT DEFINITIONS

Operating Conditions

All defect tests performed at T = 25°C.

Table 5. SPECIFICATIONS

Classification	Point Defect		Cluster Defect		Column Defect	
	Total	Zone A	Total	Zone A	Total	Zone A
C2	≤ 10	≤ 5	≤ 4	≤ 2	0	0

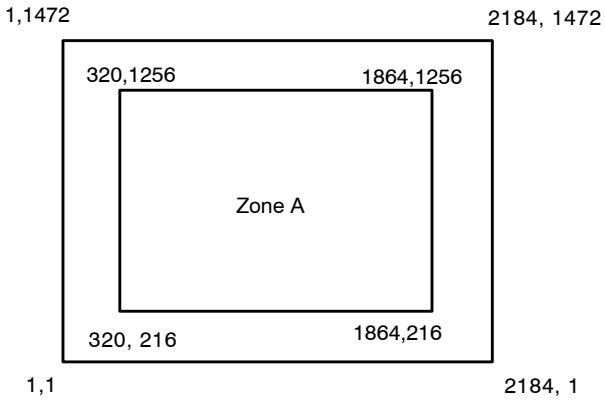


Figure 6. Active Pixel Region

Point Defects

Dark: A pixel that deviates by more than 6% from neighboring pixels when illuminated to 70% of saturation.

−or−

Bright: A pixel with a dark current greater than 15000 e^-/pixel/sec at 25°C.

Cluster Defect

A grouping of not more than 5 adjacent point defects.

Column Defect

A grouping of > 5 contiguous point defects along a single column.

A column containing a pixel with dark current > 12,000 e^-/pixel/sec (bright column).

−or−

A column column that does not meet the minimum vertical CCD charge capacity (low charge capacity column).

−or−

A column which loses more than 250 e^- under 2 ke^- illumination (trap defect).

Neighboring Pixels

The surrounding 128 x 128 pixels or ±64 column/rows.

Defect Separation

Column and cluster defects are separated by no less than two (2) pixels in any direction (excluding single pixel defects).

OPERATION

Table 6. ABSOLUTE MAXIMUM RATINGS

Description	Symbol	Minimum	Maximum	Units	Notes
Diode Pin Voltages	Vdiode	0	20	V	1, 2
Gate Pin Voltages − Type 1	Vgate1	−16	16	V	1, 3
Gate Pin Voltages − Type 2	Vgate2	0	16	V	1, 4
Inter−Gate Voltages	Vg−g		16	V	5
Output Bias Current	I_{out}		−10	mA	6
Output Load Capacitance	Cload		15	pF	6
Operating Temperature	T_{OP}	−60	60	°C	
Humidity	RH	5	90	%	7

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Referenced to pin SUB.
2. Includes pins: VRD, VDD, VSS, VOUT.
3. Includes pins: φV1, φV2, φH1, φH2.
4. Includes pins: VOG, φR.
5. Voltage difference between overlapping gates. Includes: φV1 to φV2, φH1 to φH2, φV2 to φH1, φH2 to VOG.
6. Avoid shorting output pins to ground or any low impedance source during operation.
7. T = 25°C. Excessive humidity will degrade MTTF.

Table 7. DC BIAS OPERATING CONDITIONS

Description	Symbol	Minimum	Nominal	Maximum	Units	Maximum DC Current (mA)	Notes
Reset Drain	VRD	11.0	12.0	12.25	V	0.01	
Output Amplifier Return	VSS	2.5	3.0	3.2	V	−0.5	
Output Amplifier Supply	VDD	14.5	15.0	15.25	V	I_{OUT}	
Substrate	VSUB	0	0	0	V	0.01	
Output Gate	VOG	4.75	5.0	5.5	V	0.01	
Guard	VGUARD	9.0	10.0	12.0	V		
Video Output Current	I_{OUT}		−5.0	−10.0	mA		1

1. An output load sink must be applied to Vout to activate output amplifier − see Figure 3.

AC Operating Conditions

Table 8. CLOCK LEVELS

Description	Symbol	Level	Minimum	Nominal	Maximum	Units	Effective Capacitance
Vertical CCD Clock − Phase 1	φV1	Low	−10.0	−8.5	−8.5	V	5 nF (all φV1 pins)
Vertical CCD Clock − Phase 1	φV1	High	0.0	2.0	3.0	V	5 nF (all φV1 pins)
Vertical CCD Clock − Phase 2	φV2	Low	−10.0	−8.5	−8.5	V	5 nF (all φV2 pins)
Vertical CCD Clock − Phase 2	φV2	High	0.0	2.0	3.0	V	5 nF (all φV2 pins)
Horizontal CCD Clock − Phase 1	φH1	Low	−3.5	−3.0	−2.0	V	150 pF
Horizontal CCD Clock − Phase 1	φH1	High	φH1 Low + 10	7.0	φH1 Low + 10	V	150 pF
Horizontal CCD Clock − Phase 2	φH2	Low	−3.5	−3.0	−2.0	V	150 pF
Horizontal CCD Clock − Phase 2	φH2	High	φH2 Low + 10	7.0	φH2 Low + 10	V	150 pF
Reset Clock	φR	Low	3.0	4.0	4.25	V	5 pF
Reset Clock	φR	High	10.0	11.0	11.25	V	5 pF

1. All pins draw less than 10 μA DC current.

TIMING

Table 9. REQUIREMENTS AND CHARACTERISTICS

Description	Symbol	Minimum	Nominal	Maximum	Units	Notes
φH1, φH2 Clock Frequency	f_H		10	12	MHz	1, 2, 3
Pixel Period (1 count)	t_e	67	100		ns	
φH1, φH2 Setup Time	$t_{\varphi HS}$	0.5	1		μs	
φV1, φV2 Clock Pulse Width	$t_{\varphi V}$	4	5		μs	2
Reset Clock Pulse Width	$t_{\varphi R}$	5	20		ns	4
Readout Time	$t_{readout}$	252.5	366.3		ms	5
Integration Time	t_{int}					6
Line Time	t_{line}	167.2	242.6		μs	7

1. 50% duty cycle values.
2. CTE may degrade above the nominal frequency.
3. Rise and fall times (10/90% levels) should be limited to 5−10% of clock period. Cross−over of register clocks should be between 40−60% of amplitude.
4. φR should be clocked continuously.
5. $t_{readout} = (1510 * t_{line})$
6. Integration time is user specified. Longer integration times will degrade noise performance due to dark signal fixed pattern and shot noise.
7. $t_{line} = (3 * t_{\varphi V}) + t_{\varphi HS} + (2267) + t_{e-}$

Frame Timing

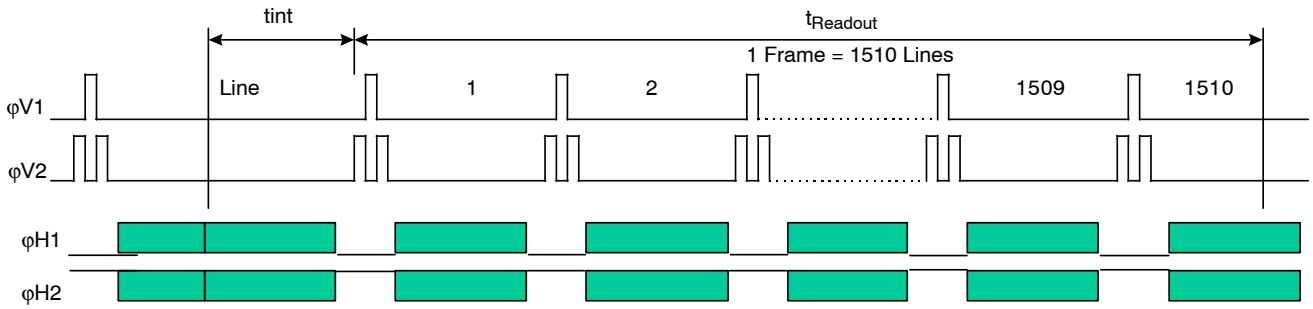


Figure 7. Frame Timing

Line Timing (Each Output)

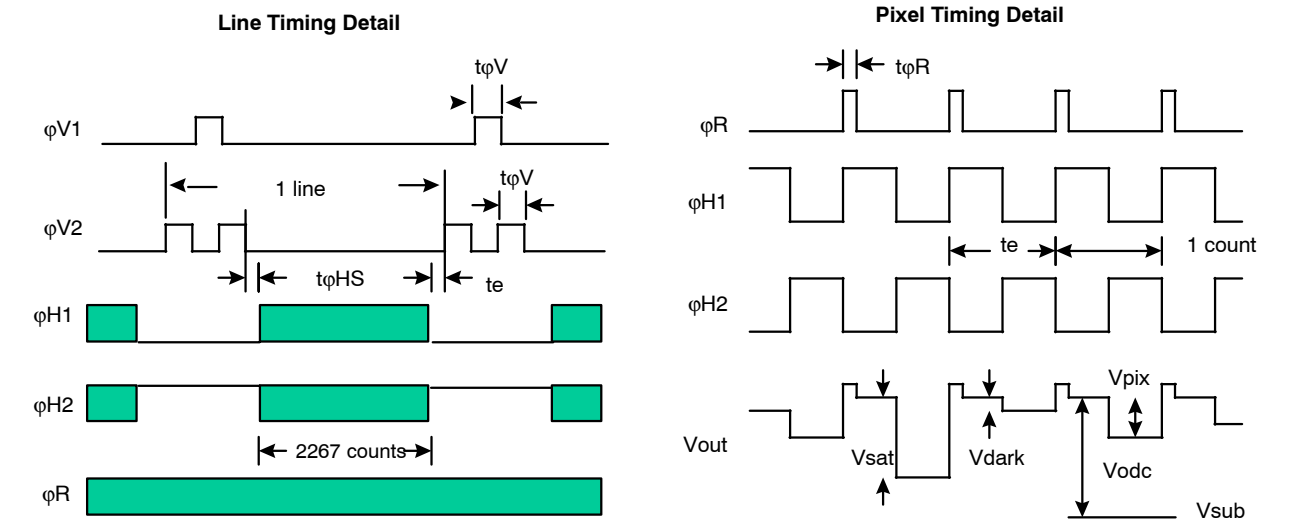
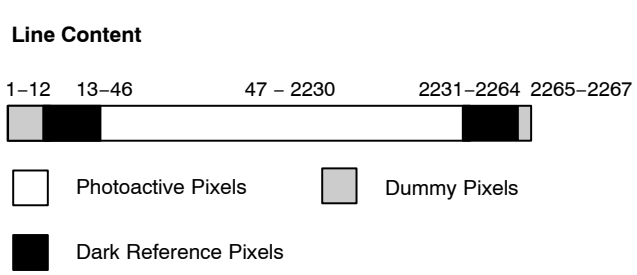


Figure 8. Line Timing



Vsat	Saturated pixel video output signal
Vdark	Video output signal in no light situation, not zero due to Jdark
Vpix	Pixel video output signal level, more electrons =more negative*
Vodc	Video level offset with respect to vsub
Vsub	Analog Ground

* See Image Aquisition section (page 4)

Figure 9. Timing Diagrams

NOTE: The KAF−3200 was designed to be compatible with the KAF−1602 and KAF−0401 series of image sensors. Please note that the polarities of the two−phase clocks have been swapped on the KAF−3200 compared to the KAF−1602 and KAF−0401.

STORAGE AND HANDLING

Table 10. STORAGE CONDITIONS

Description	Symbol	Minimum	Maximum	Units	Notes
Storage Temperature	T_{ST}	−20	80	°C	1
Humidity	RH	5	90	%	2

1. Storage toward the maximum temperature will accelerate color filter degradation.
2. T = 25°C. Excessive humidity will degrade MTTF.

For information on ESD and cover glass care and cleanliness, please download the *Image Sensor Handling and Best Practices* Application Note (AN52561/D) from www.onsemi.com.

For information on soldering recommendations, please download the Soldering and Mounting Techniques Reference Manual (SOLDERRM/D) from www.onsemi.com.

For quality and reliability information, please download the *Quality & Reliability* Handbook (HBD851/D) from www.onsemi.com.

For information on device numbering and ordering codes, please download the *Device Nomenclature* technical note (TND310/D) from www.onsemi.com.

For information on Standard terms and Conditions of Sale, please download Terms and Conditions from www.onsemi.com.

MECHANICAL INFORMATION

Completed Assembly

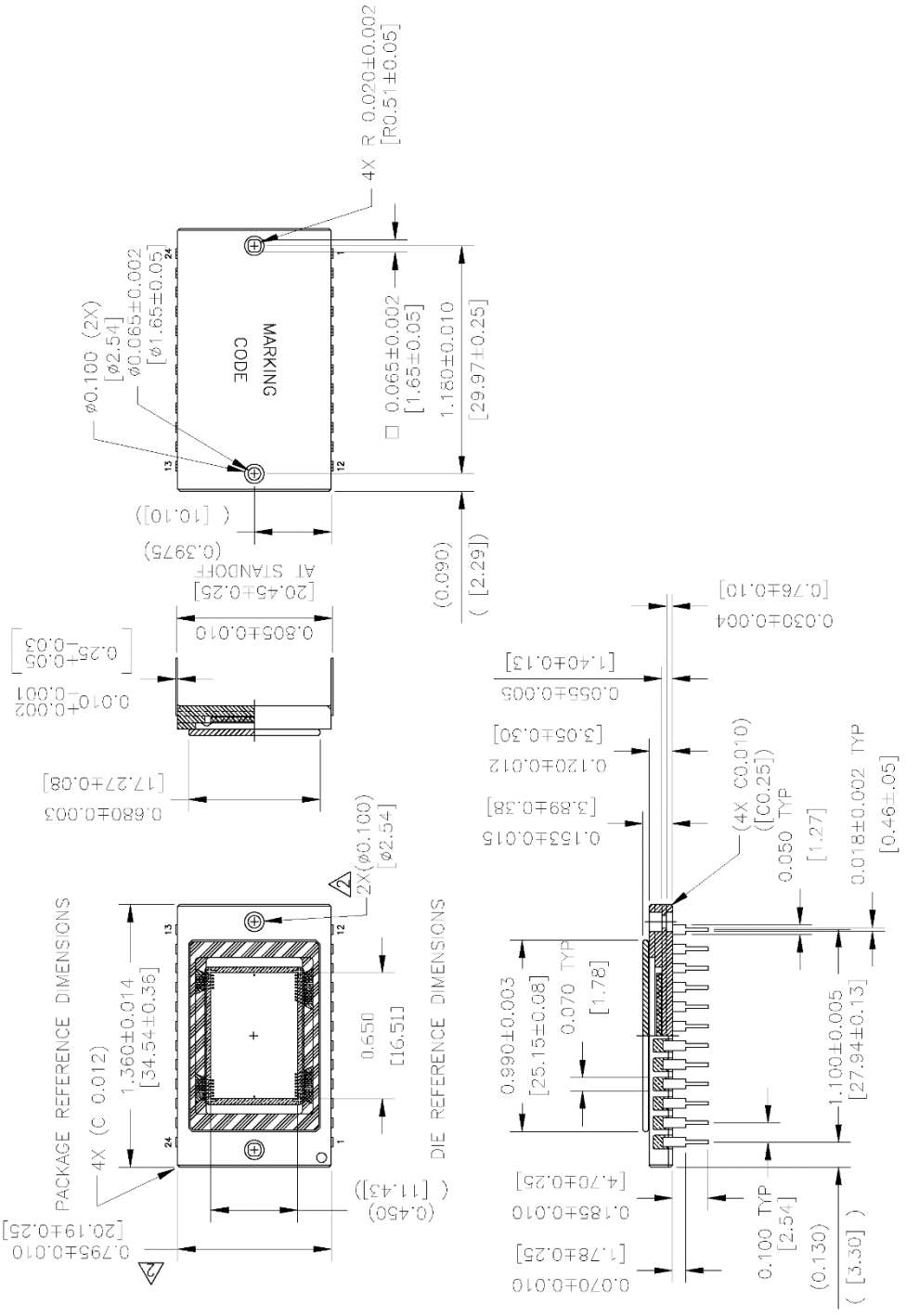


Figure 10. Completed Assembly (1 of 2)

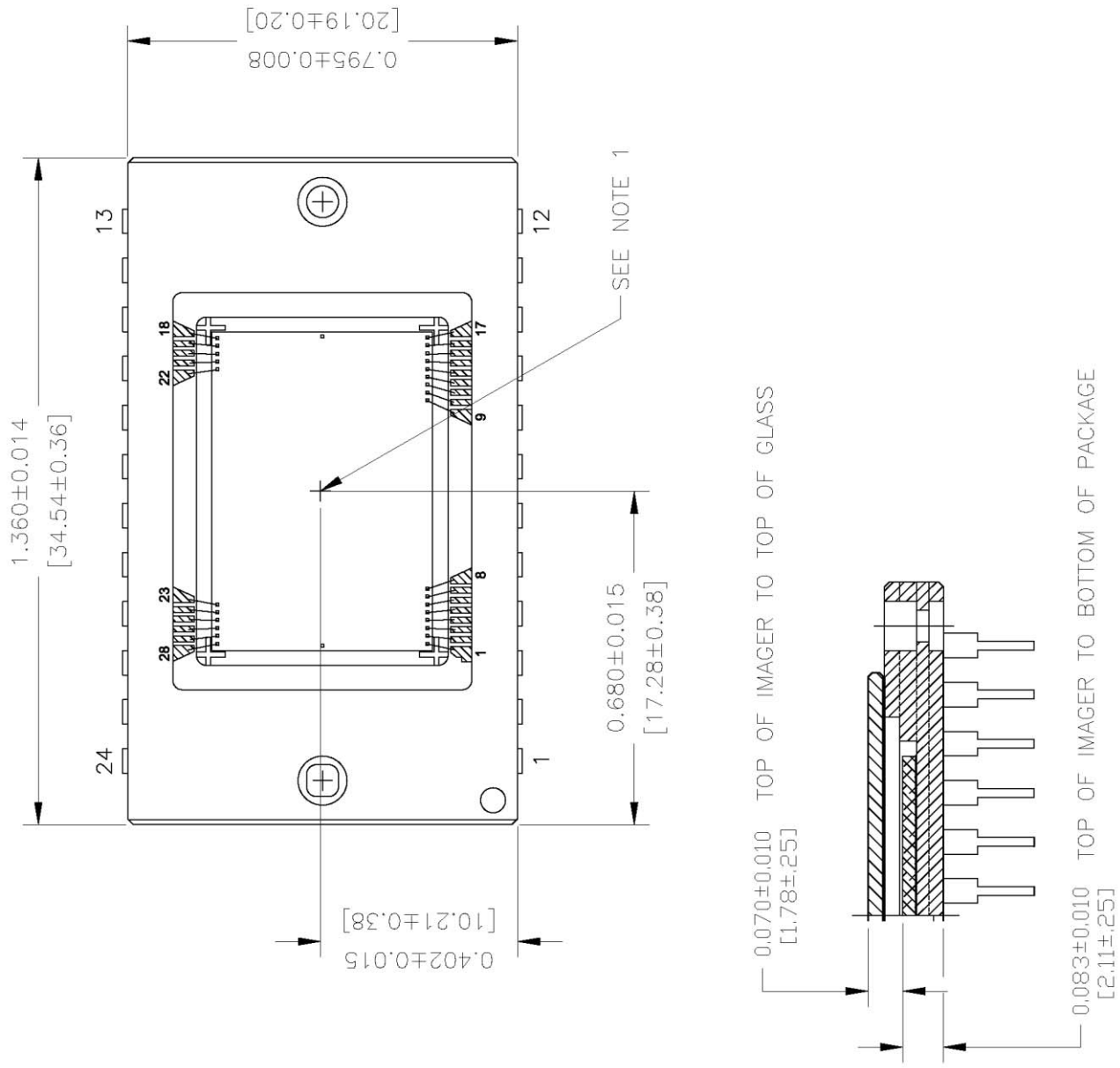


Figure 11. Completed Assembly (2 of 2)

AR Cover Glass Transmission

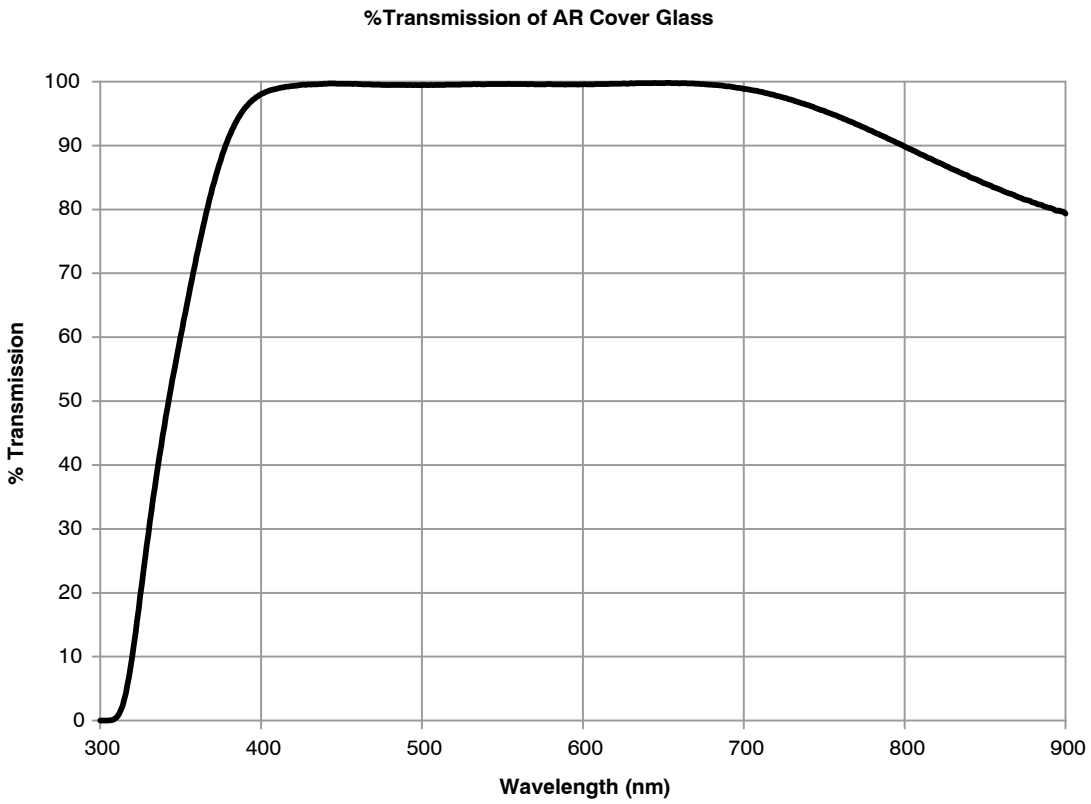


Figure 12. Antireflective Cover Glass Transmission

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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P.O. Box 5163, Denver, Colorado 80217 USA
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